ACE12350M

N-Channel 200-V (D-S) MOSFET

Features

- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

Product Summary		
V_{DS} (V)	r_{DS}(on) (mΩ)	I_D(A)
200	1500@ V_{GS} = 10V	0.77

Applications

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

Absolute Maximum Ratings

Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	200	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [a]	T_A=25°C	I_D	0.77	A
	T_A=70°C		0.60	
Pulse Drain Current [b]		I_{DM}	2	
Continuous Drain Current (Diode Continuous) [a]		I_S	1.7	A
Power Dissipation [a]	T_A=25°C	P_D	1.3	W
	T_A=70°C		0.8	
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55 to 150	°C

Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient [a]	t≦10sec	$R_{\theta JA}$	100	℃/W
	Steady State		166	℃/W

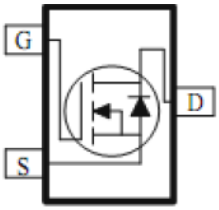
Notes

a. Surface Mounted on 1” x 1” FR4 Board.

b. Pulse width limited by maximum junction temperature

Packaging Type

SOT-23-3



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Ordering information

ACE12350M XX + H

- H: Halogen - free
- XX: Pb - free
- ACE12350M: BM: SOT-23-3

Electrical Characteristics

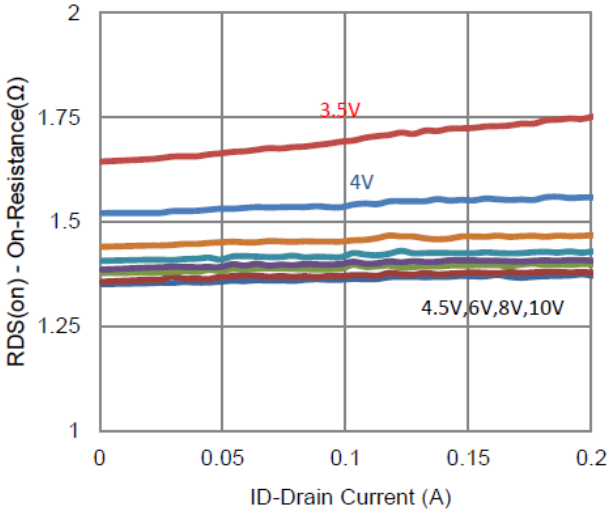
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Source Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1			V
Gate Body Leakage	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=160V, V_{GS}=0V			1	uA
		V_{DS}=160V, V_{GS}=0V, T_J=55℃			10	
On-State Drain-Current [a]	$I_{D(on)}$	V_{DS}=5V, V_{GS}=10V	1.2			A
Static Drain-Source On-Resistance [a]	$r_{DS(ON)}$	V_{GS}=10V,I_D=0.3A			1500	mΩ
Forward Transconductance [a]	g_{fS}	V_{DS}=15V,I_D=0.3A		3		S
Diode Forward Voltage [a]	V_{SD}	I_S=0.85A ,V_{GS}=0V		0.8		V
Dynamic [b]						
Total Gate Charge	Q_g	V_{DS}=100V, V_{GS}=10V, I_D=0.3A		5.3		nC
Gate-Source Charge	Q_{gs}			0.9		
Gate-Drain Charge	Q_{gd}			1.4		
Turn-On Delay Time	$t_{d(on)}$	V_{DS}=100V, ,R_L=300Ω I_D=0.33A ,V_{GEN}=10V R_{GEN}=6Ω,		3		ns
Rise Time	t_f			4		
Turn-Off Delay Time	$t_{d(off)}$			14		
Fall Time	t_f			8		
Input Capacitance	C_{iss}	V_{DS}=15V, V_{GS}=0V f=1MHz		163		pF
Output Capacitance	C_{oss}			12		
Reverse Transfer Capacitance	C_{rss}			11		

Note:

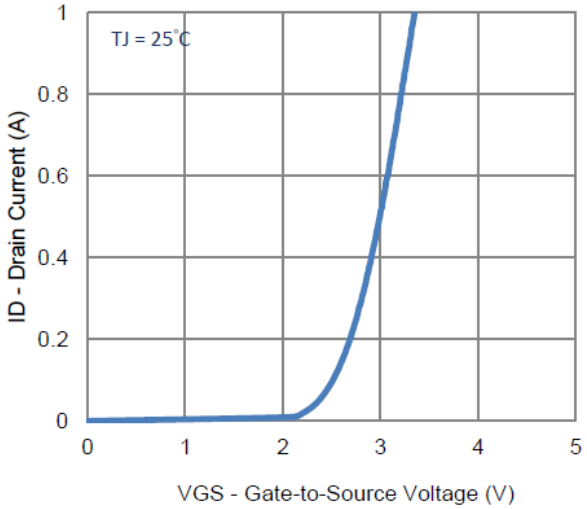
a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.

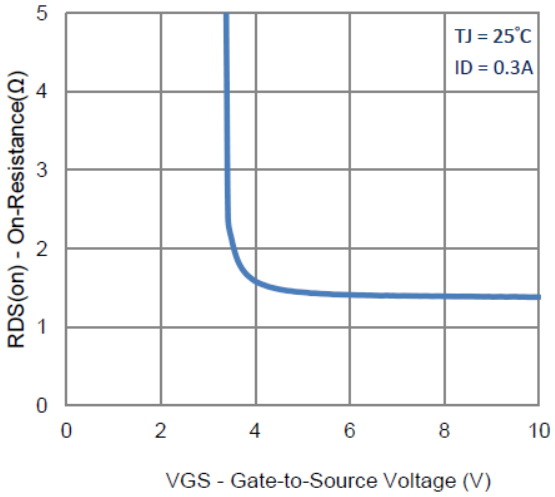
Typical Electrical Characteristics



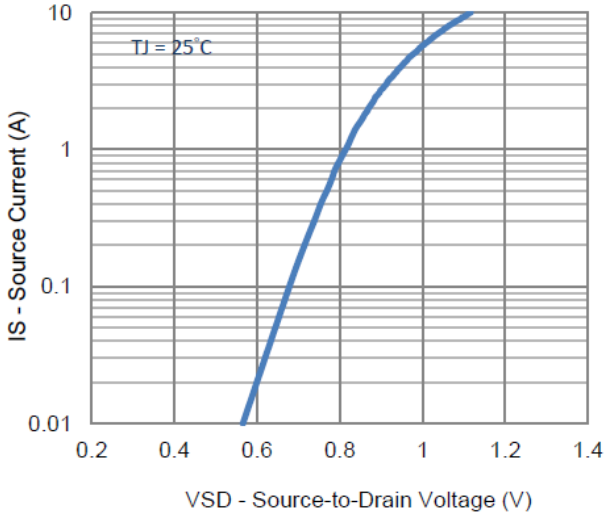
1. On-Resistance vs. Drain Current



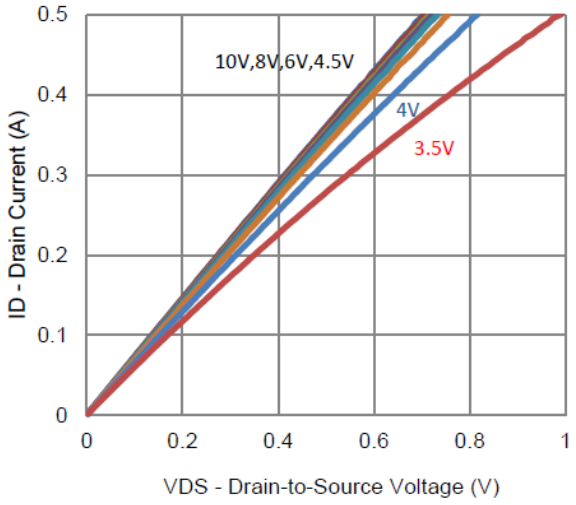
2. Transfer Characteristics



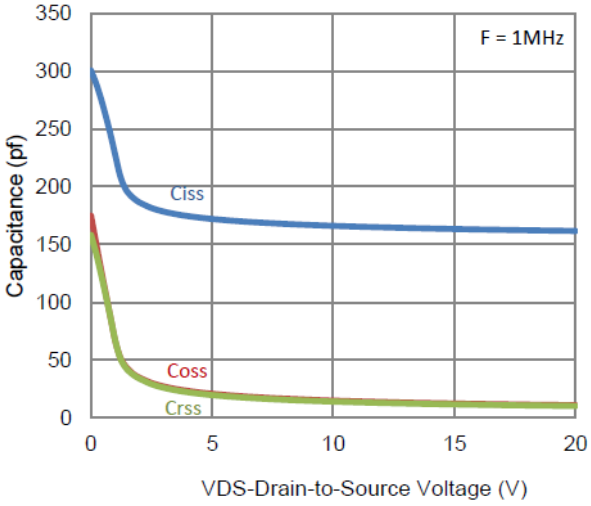
3. On-Resistance vs. Gate-to-Source Voltage



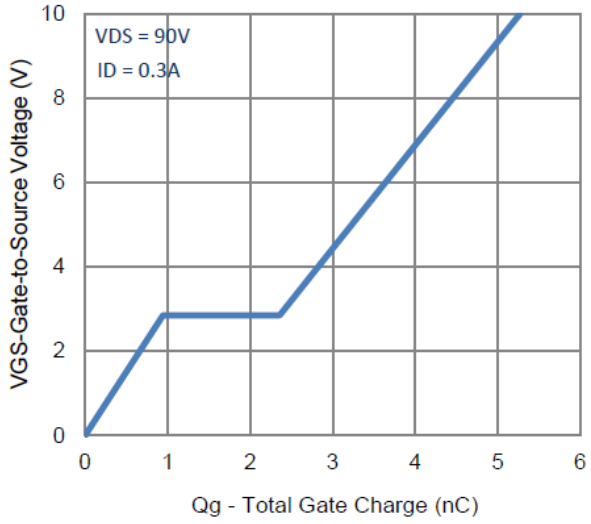
4. Drain-to-Source Forward Voltage



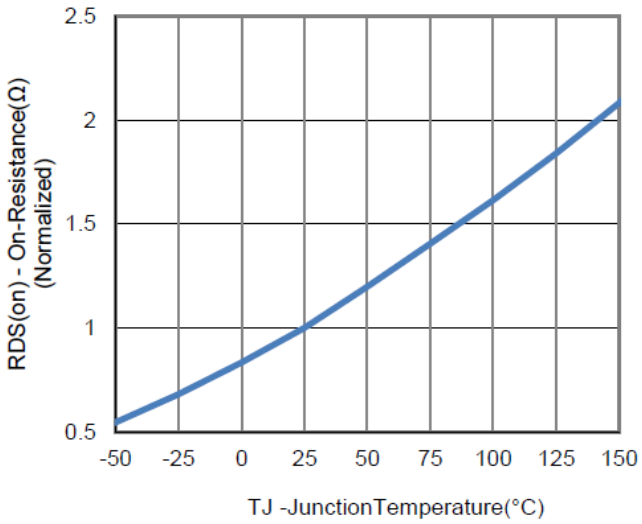
5. Output Characteristics



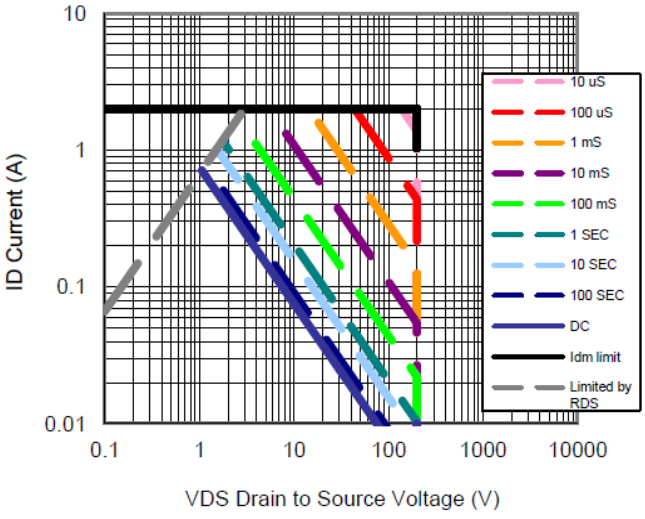
6. Capacitance



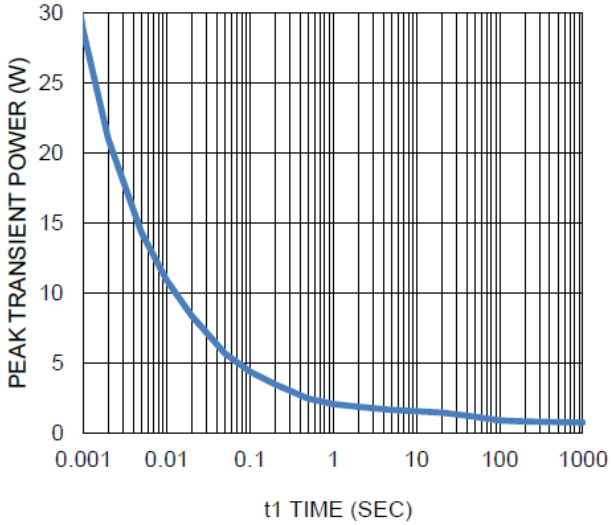
7. Gate Charge



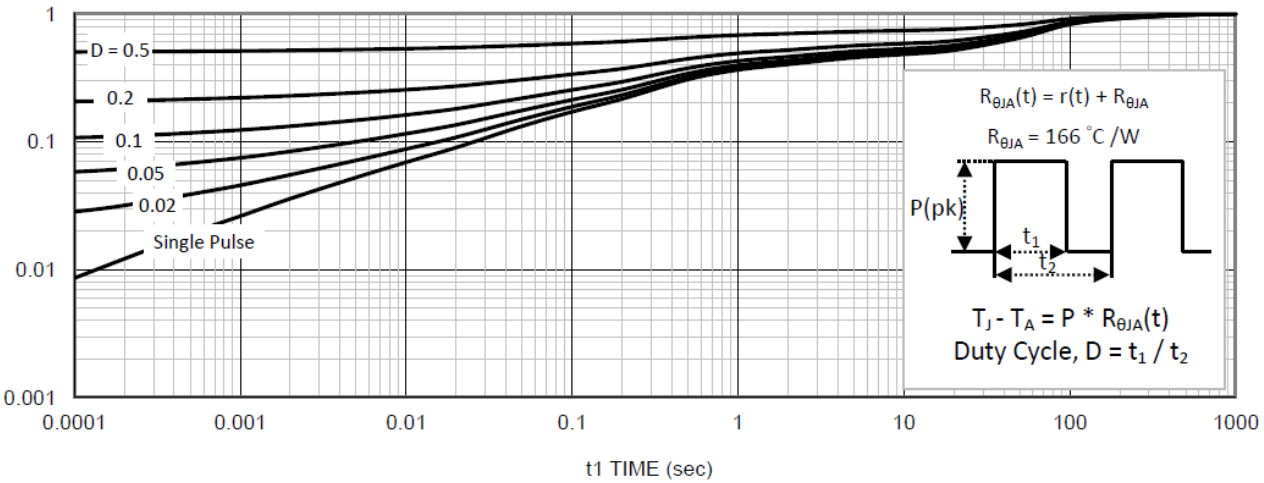
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area



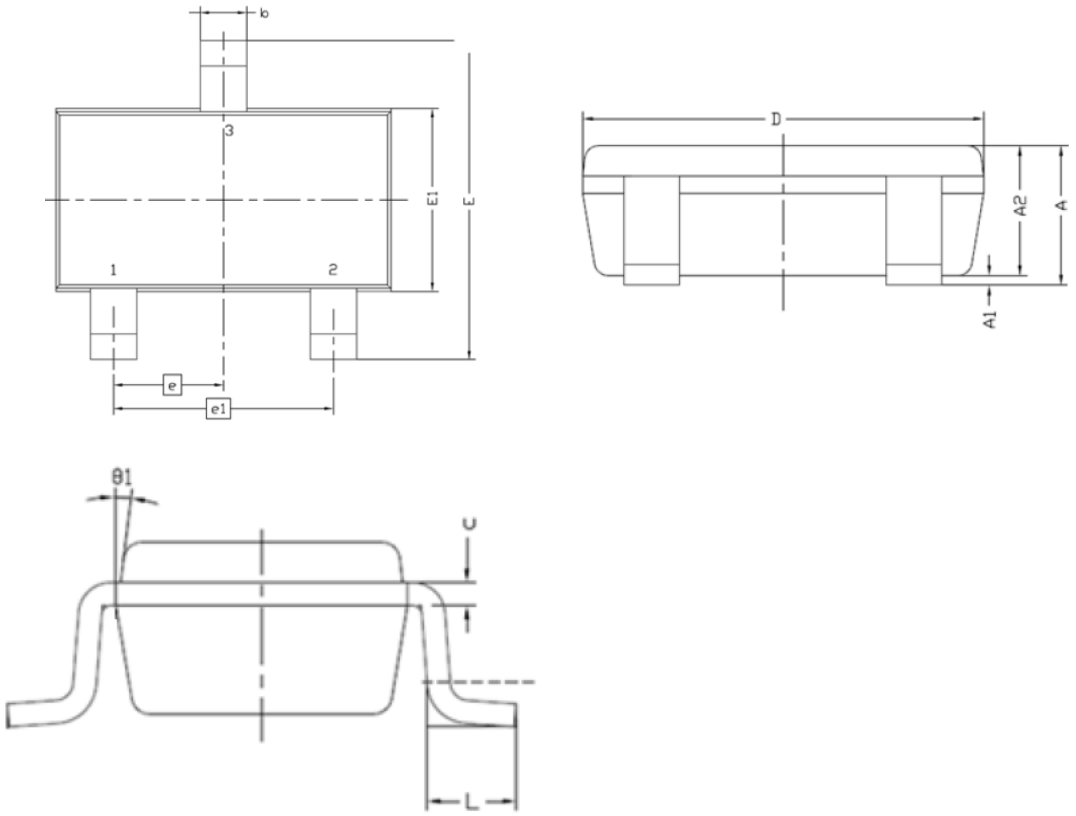
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Packing Information

SOT-23-3



Symbols	Millimeters	
	Min	Max
A	0.8	1.2
A1	0	0.1
A2	0.7	1.1
b	0.3	0.5
C	0.1	0.2
D	2.7	3.1
E	2.6	3
E1	1.4	1.8
e	0.95 BSC	
e1	1.9BSC	
L	0.3	0.6
θ1	7 ◦ NOM	

Notes

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1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and shoes failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.